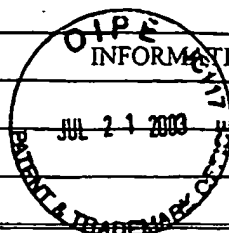
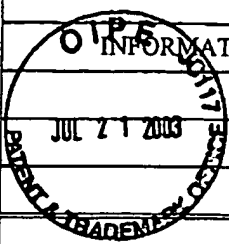


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 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)					M-11822 US		09/925,102	
					Applicant(s) Jack H. Yuan et al.			
					Filing Date		Group	
					August 8, 2001		2185	
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							Translation	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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						Jack H. Yuan et al.			
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GLM/CAJ:ka 05/11/05 6115-58351-01 373314

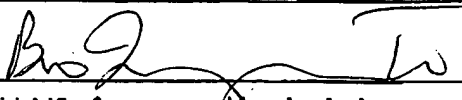
INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Attorney Docket Number	6115-58351-01
Application Number	09/925,125
Filing Date	August 9, 2001
First Named Inventor	Scheurich
Art Unit	2162
Examiner Name	Baoquoc N. To

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Copies of U.S. Patent documents do not need to be provided, unless requested by the Patent and Trademark Office. For patents, provide the patent number and the issue date. For published U.S. applications, provide the publication number and the publication date. For unpublished pending patent applications, provide the application number and the filing date.

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Information Disclosure Statement (1449) Page 1 of 1